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In re application of

Hisayuki MIKI, et al.

Appln. No.: 09/900,962

Group Art Unit: 2812

Confirmation No.: 7972

Examiner: Savitri Mulpun

Filed: July 10, 2001

For: METHOD FOR PRODUCING P-TYPE GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR,
METHOD FOR PRODUCING GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-
EMITTING DEVICE

PAPERS FILED ENTITLED:

1. **Supplemental Amendment (4 pages including appendix showing changes made)**

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DOCKET NO.: Q61744

ATTORNEY/SEC: AJR/KKT/sls

Date Filed: June 12, 2003

WASHINGTON OFFICE



23373

PATENT TRADEMARK OFFICE

PATENT APPLICATION**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q61744

Hisayuki MIKI, et al.

Appln. No.: 09/900,962

Group Art Unit: 2812

Confirmation No.: 7972

Examiner: Savitri Mulpuri

Filed: July 10, 2001

For: METHOD FOR PRODUCING P-TYPE GALLIUM NITRIDE-BASED COMPOUND
SEMICONDUCTOR, METHOD FOR PRODUCING GALLIUM NITRIDE-BASED
COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE

SUPPLEMENTAL AMENDMENT**MAIL STOP NON-FEE AMENDMENT**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This Amendment is supplemental to the Amendment Under 37 C.F.R. § 1.111
filed on February 12, 2003.

Please amend this application as follows:

IN THE CLAIMS:**Please enter the following amended claims**

8. (twice amended) A method for producing a gallium nitride-based compound semiconductor light-emitting device comprising providing an n-type layer and a light-emitting layer each comprising a gallium nitride-based compound semiconductor, providing a p-type layer comprising a gallium nitride-based compound semiconductor through the following steps:

producing a gallium nitride-based compound semiconductor layer doped with a p-type impurity;